

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SK2869

Silicon N Channel MOS FET  
High Speed Power Switching

**RENESAS**

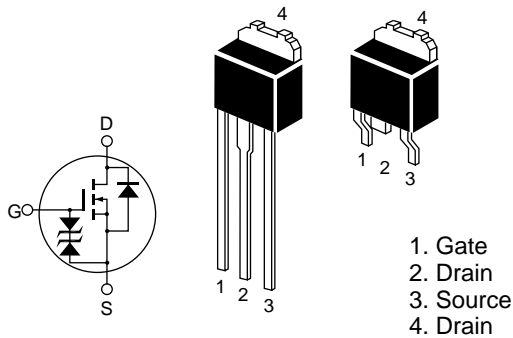
ADE-208-570 (Z)  
1st. Edition  
Sep. 1997

## Features

- Low on-resistance  
 $R_{DS} = 0.033 \Omega$  typ.
- High speed switching
- 4V gate drive device can be driven from 5V source

## Outline

DPAK-2



**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

<b>Item</b>	<b>Symbol</b>	<b>Ratings</b>	<b>Unit</b>
Drain to source voltage	$V_{DSS}$	60	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	$I_D$	20	A
Drain peak current	$I_{D(pulse)}^{*1}$	80	A
Body to drain diode reverse drain current	$I_{DR}$	20	A
Avalanche current	$I_{AP}^{*3}$	20	A
Avalanche energy	$E_{AR}^{*3}$	34	mJ
Channel dissipation	$P_{ch}^{*2}$	30	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

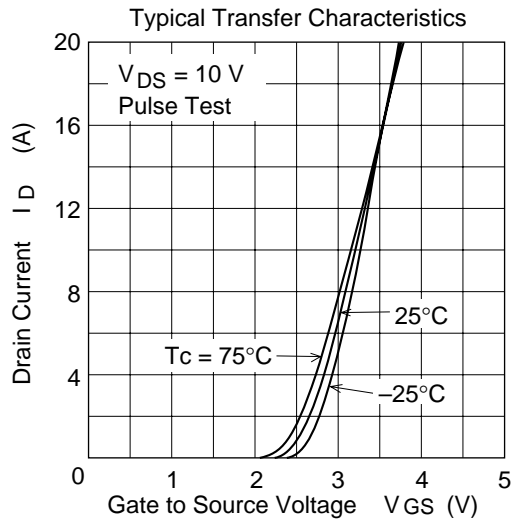
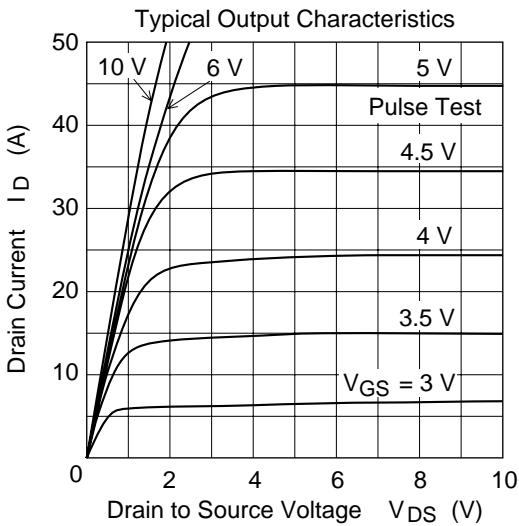
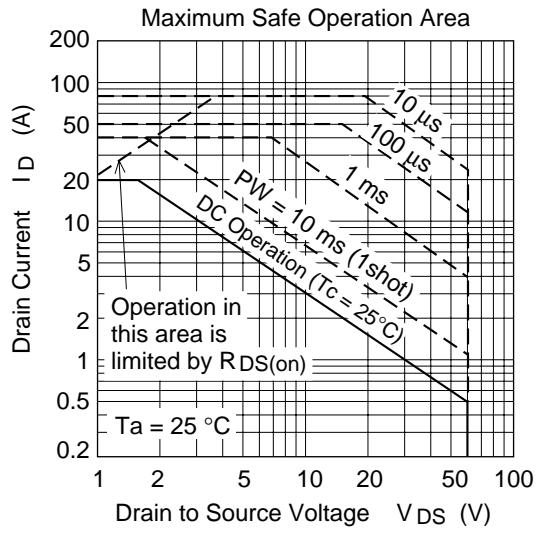
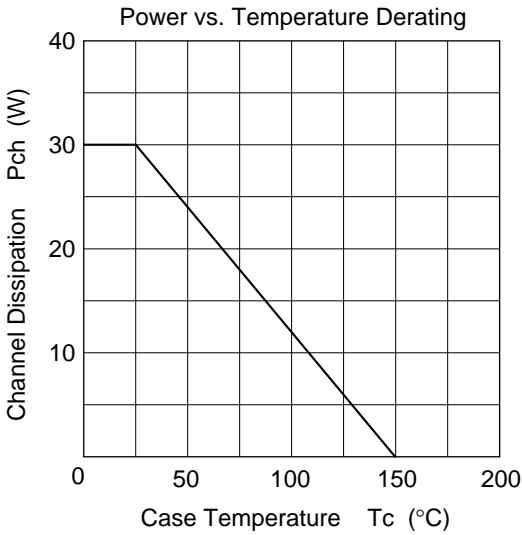
- Notes: 1.  $PW \leq 10\mu\text{s}$ , duty cycle  $\leq 1\%$   
2. Value at  $T_c = 25^\circ\text{C}$   
3. Value at  $T_{ch} = 25^\circ\text{C}$ ,  $R_g \geq 50\Omega$

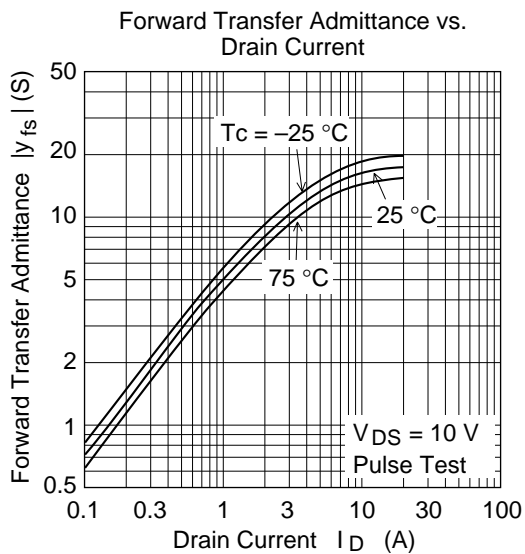
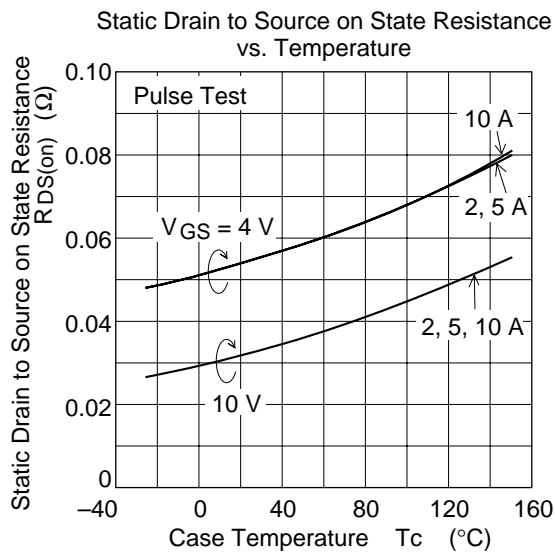
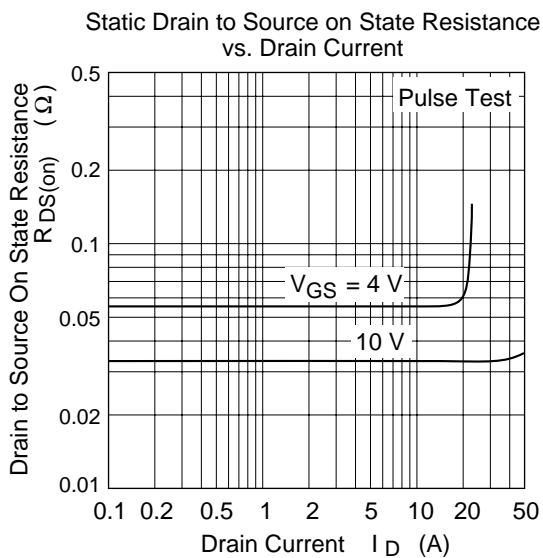
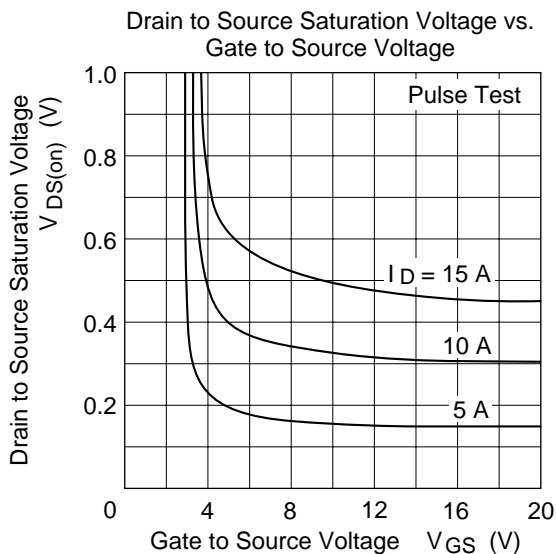
## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = ±100μA, V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = ±16V, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	10	μA	$V_{DS} = 60V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	—	2.5	V	$I_D = 1mA, V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.033	0.045	Ω	$I_D = 10A, V_{GS} = 10V^{*1}$
	$R_{DS(on)}$	—	0.055	0.07	Ω	$I_D = 10A, V_{GS} = 4V^{*1}$
Forward transfer admittance	$ y_{fs} $	10	16	—	S	$I_D = 10A, V_{DS} = 10V^{*1}$
Input capacitance	$C_{iss}$	—	740	—	pF	$V_{DS} = 10V$
Output capacitance	$C_{oss}$	—	380	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	140	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = 10A, V_{GS} = 10V$
Rise time	$t_r$	—	110	—	ns	$R_L = 3Ω$
Turn-off delay time	$t_{d(off)}$	—	105	—	ns	
Fall time	$t_f$	—	120	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1.0	—	V	$I_F = 20A, V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	40	—	V	$I_F = 20A, V_{GS} = 0$ $diF/dt = 50A/μs$

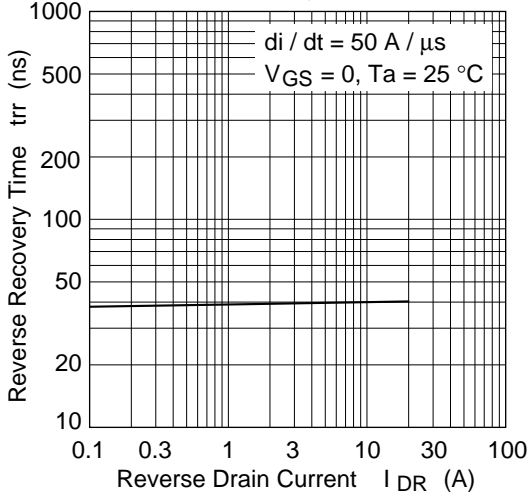
Note: 1. Pulse test

Main Characteristics

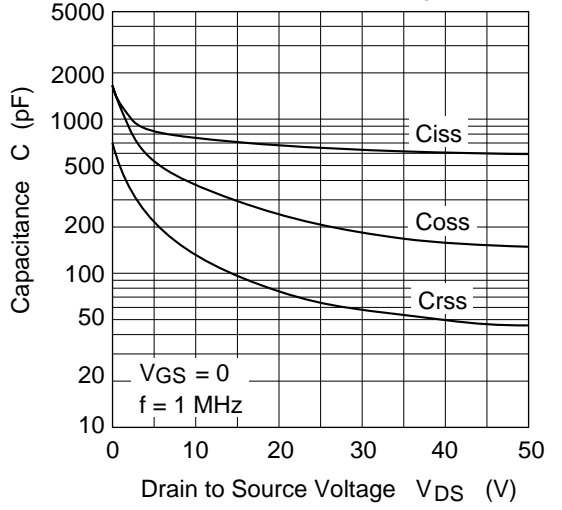




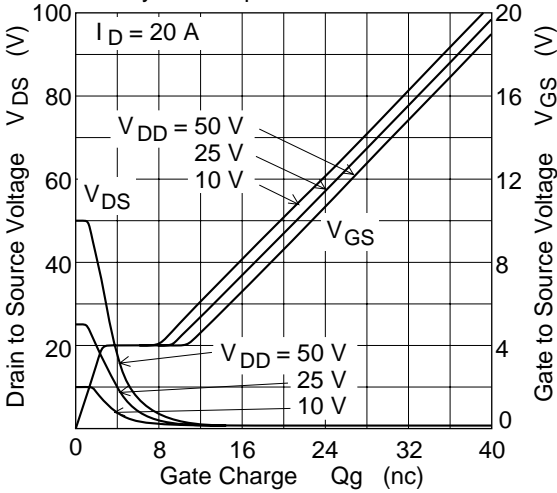
Body to Drain Diode Reverse Recovery Time



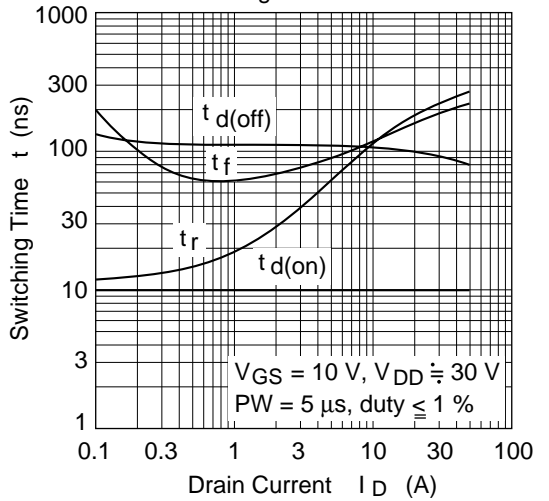
Typical Capacitance vs. Drain to Source Voltage



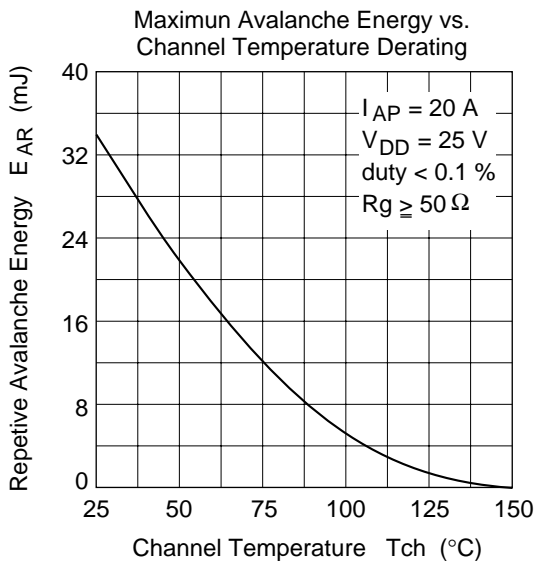
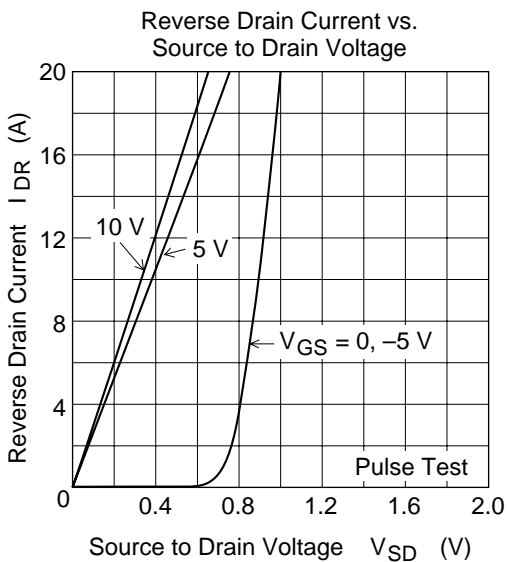
Dynamic Input Characteristics



Switching Characteristics

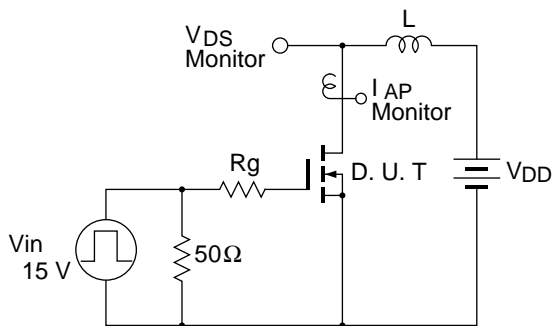




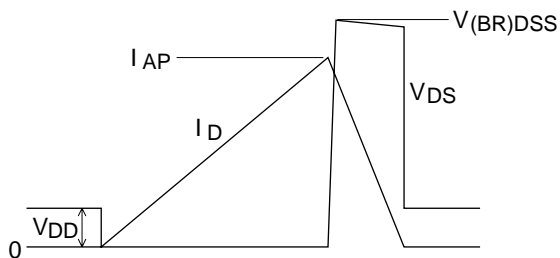


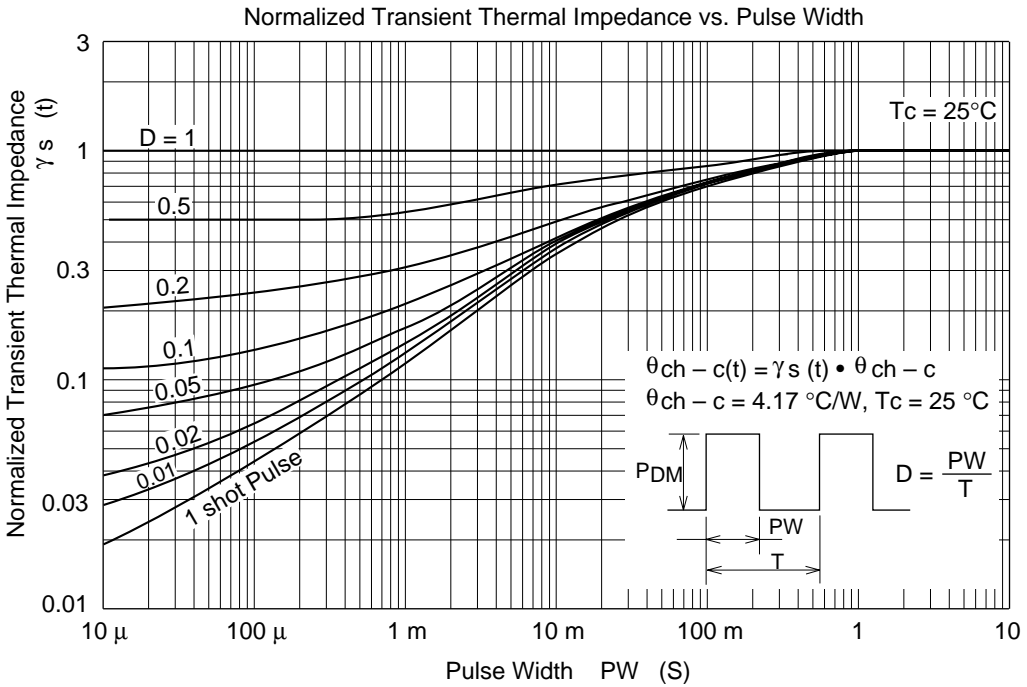
Avalanche Test Circuit

Avalanche Waveform

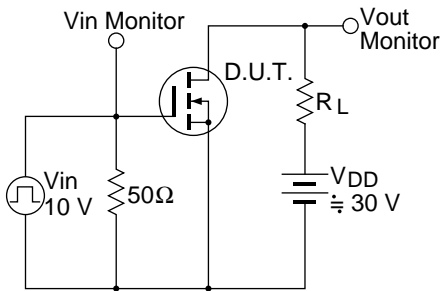


$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$

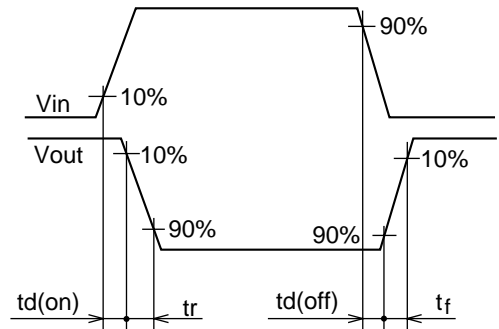




Switching Time Test Circuit



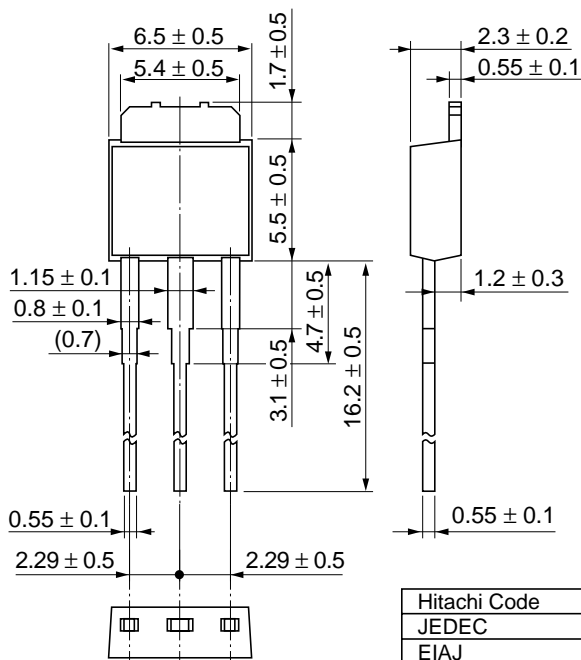
Waveform



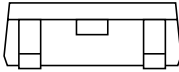
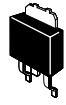
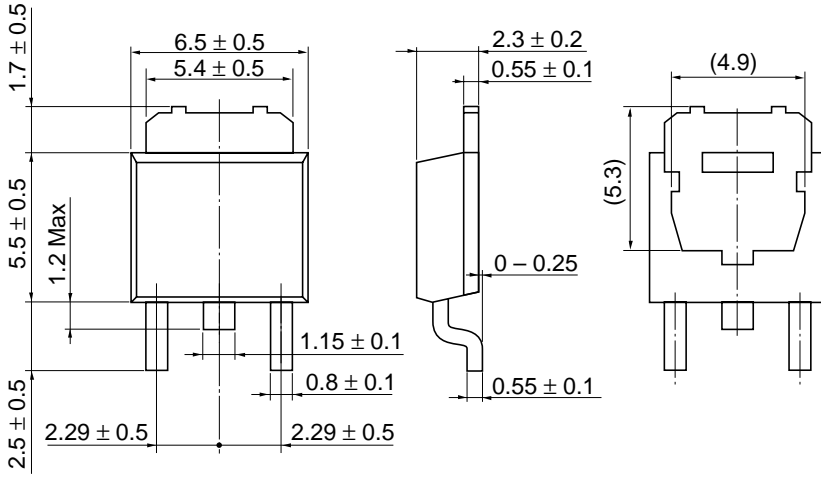
## Package Dimensions

As of January, 2001

Unit: mm



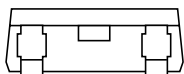
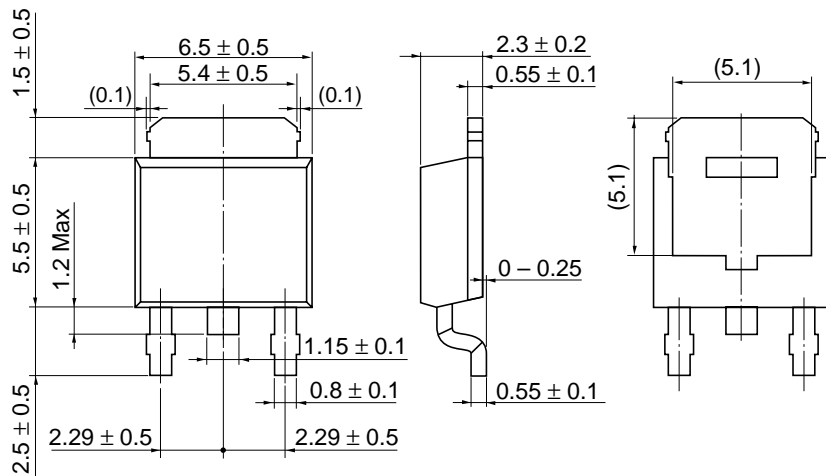
Hitachi Code	DPAK (L)-(2)
JEDEC	—
EIAJ	—
Mass (reference value)	0.42 g



Hitachi Code	DPAK (S)-(1),(2)
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.28 g

As of January, 2001

Unit: mm



Hitachi Code	DPAK (S)-(3)
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.28 g

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